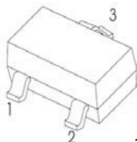




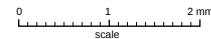
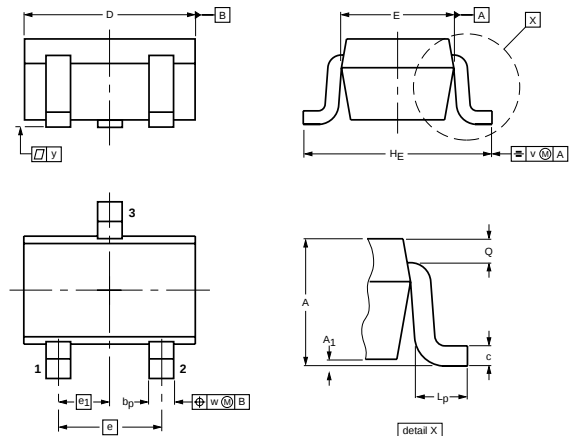
FEATURES

Complimentary to SS8550W



1.BASE
2.EMITTER
3.COLLECTOR

SOT-323



DIMENSIONS (mm are the original dimensions)

UNIT	A	A ₁ max	b _p	c	D	E	e	e ₁	H _E	L _p	Q	v	w
mm	1.1 0.8	0.1	0.4 0.3	0.25 0.10	2.2 1.8	1.35 1.15	1.3	0.65	2.2 2.0	0.45 0.15	0.23 0.13	0.2	0.2

MAXIMUM RATINGS (T_A=25°C unless otherwise noted)

Symbol	Parameter	Value	Units
V _{CBO}	Collector-Base Voltage	40	V
V _{CEO}	Collector-Emitter Voltage	25	V
V _{EBO}	Emitter-Base Voltage	5	V
I _C	Collector Current -Continuous	1.5	A
P _C	Collector Power Dissipation	0.2	W
T _j	Junction Temperature	150	°C
T _{stg}	Storage Temperature	-55-150	°C

SS8050W

ELECTRICAL CHARACTERISTICS (Tamb=25°C unless otherwise specified)

Parameter	Symbol	Test conditions	MIN	TYP	MAX	UNIT
Collector-base breakdown voltage	$V_{(BR)CBO}$	$I_C = 100\mu A, I_E = 0$	40			V
Collector-emitter breakdown voltage	$V_{(BR)CEO}$	$I_C = 0.1mA, I_B = 0$	25			V
Emitter-base breakdown voltage	$V_{(BR)EBO}$	$I_E = 100\mu A, I_C = 0$	5			V
Collector cut-off current	I_{CBO}	$V_{CB} = 40V, I_E = 0$			0.1	μA
Collector cut-off current	I_{CEO}	$V_{CB} = 20V, I_E = 0$			0.1	μA
Emitter cut-off current	I_{EBO}	$V_{EB} = 5V, I_C = 0$			0.1	μA
DC current gain	$h_{FE(1)}$	$V_{CE} = 1V, I_C = 100mA$	120		400	
	$h_{FE(2)}$	$V_{CE} = 1V, I_C = 800mA$	40			
Collector-emitter saturation voltage	$V_{CE(sat)}$	$I_C = 800mA, I_B = 80mA$			0.5	V
Base-emitter saturation voltage	$V_{BE(sat)}$	$I_C = 800mA, I_B = 80mA$			1.2	V
Transition frequency	f_T	$V_{CE} = 10V, I_C = 50mA$ $f = 30MHz$	100			MHz

CLASSIFICATION OF $h_{FE(1)}$

RANK	L	H	J
RANGE	120 - 200	200 - 350	300 - 400

RATING AND CHARACTERISTIC CURVES (SS8050W)

